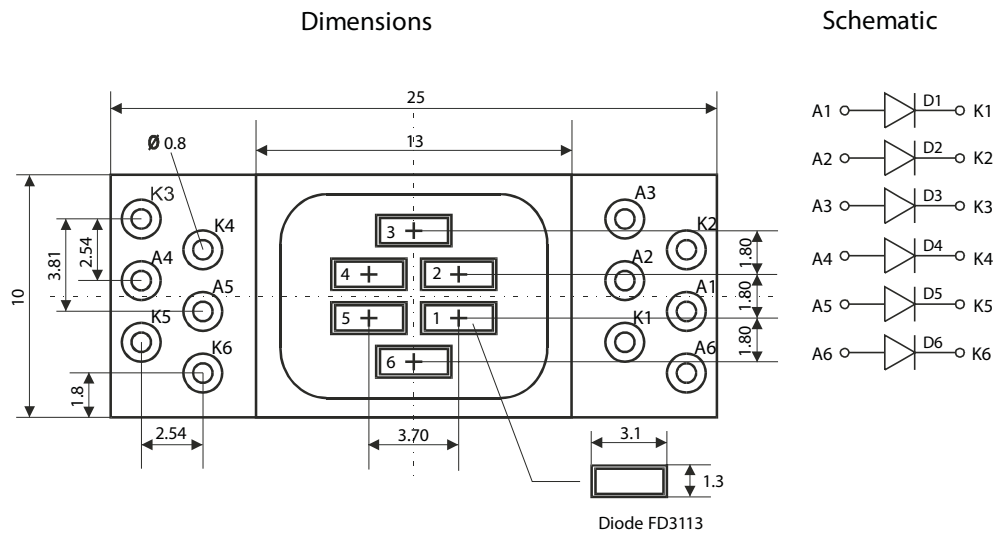


FEATURES

- High responsivity
- Low capacitance
- High reliability
- Peak wavelength at 830 nm

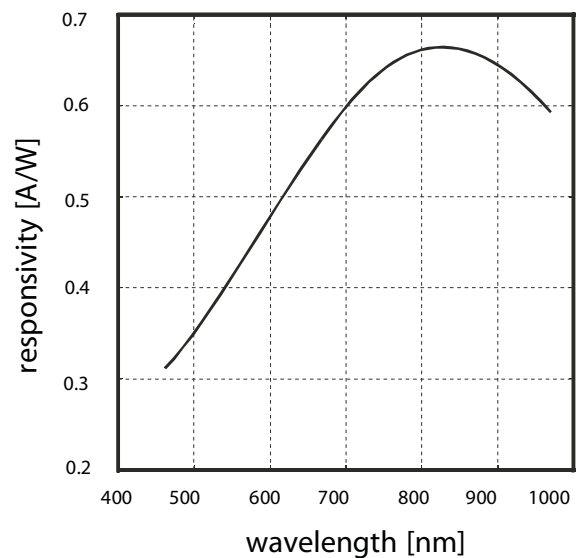


DESCRIPTION

The photosensor is made of 6-chip photodiode array. Photodiodes (FD3113) are produced in planar technology and passivated with silicon-nitride. Silicon-nitride is acting as antireflective layer. Photodiodes are bonded to the PCB and protected with transparent epoxy glue. The photodiode can work in photovoltaic or photoconductive mode.

TEMPERATURE CONDITIONS

| | |
|-----------|----------------|
| Storage | 0 °C...+70 °C |
| Operating | 0 °C...+70 °C |
| Soldering | Hand soldering |



PHOTODIODE CHARACTERISTICS

| PRODUCT | DIMENSIONS | | ELECTRICAL PARAMETERS | | | | OPTICAL PARAMETERS | | |
|---------|------------|-------------|-----------------------|-------------------|-------------|-------------|--------------------|----------|-------------|
| | CHIP SIZE | ACTIVE AREA | DARK CURRENT | BV | CAPACITANCE | | PEAK | RESPONSE | CURRENT |
| TYPE | (mm) | (mm) | $V_r = -5V$ | $I_r > -50 \mu A$ | $V_r = 0V$ | $V_r = -5V$ | I | | |
| | | | TYP | MIN | TYP | TYP | TYP | TYP | TYP |
| | | | (nA) | (V) | (pF) | (pF) | (nm) | (A/W) | (μA) |
| FD 3113 | 3.1 x 1.3 | 3.10 | <1 | 50 | 52 | 23 | 830 | 0.67 | 1000 |

Note 1: CURRENT (I_{sc}) is measured under 100 mW/cm² AM spectrum.